

June 2018

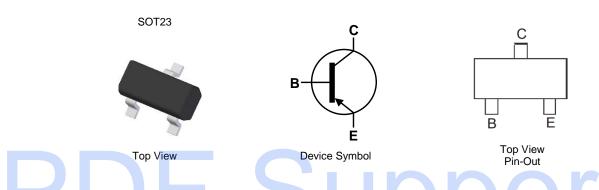
40V PNP SMALL SIGNAL TRANSISTOR IN SOT23

Features

- **Epitaxial Planar Die Construction**
- Ideal for Medium Power Amplification and Switching
- Complementary NPN Type: MMBT3904
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (23)
- Weight: 0.008 grams (Approximate)



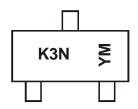
Ordering Information (Notes 4 & 5)

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Product	Status	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
MMBT3906-7-F	Active	AEC-Q101	K3N	7	8	3000
MMBT3906Q-7-F	Active	Automotive	K3N	7	8	3000
MMBT3906Q-13-F	Active	Automotive	K3N	13	8	10,000
MMBT3906-13-F	Active	AEC-Q101	K3N	13	8	10.000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



K3N = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: E= 2017) M or \overline{M} = Month (ex: 9 = September)

Date Code Key

Year	2015	20	016	2017	2	2018	2019		2020	2021		2022
Code	С		D	Е		F	G		Н			J
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-40	V
Collector-Emitter Voltage	V _{CEO}	-40	V
Emitter-Base Voltage	V _{EBO}	-6.0	V
Collector Current	Ic	-200	mA
Peak Collector Current	Ісм	-200	mA
Peak Base Current	I _{BM}	-100	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 6)	5	310	mW
rowei Dissipation	(Note 7)	P_{D}	350	IIIVV
Thermal Decistores, Junction to Ambient	(Note 6)	5	403	°C/W
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{\Theta JA}$	R _{OJA} 357	
Thermal Resistance, Junction to Leads	(Note 8)	ReJL	350	°C/W
Operating and Storage Temperature Range		$T_{J_i}T_{STG}$	-55 to +150	°C

ESD Ratings (Note 9)

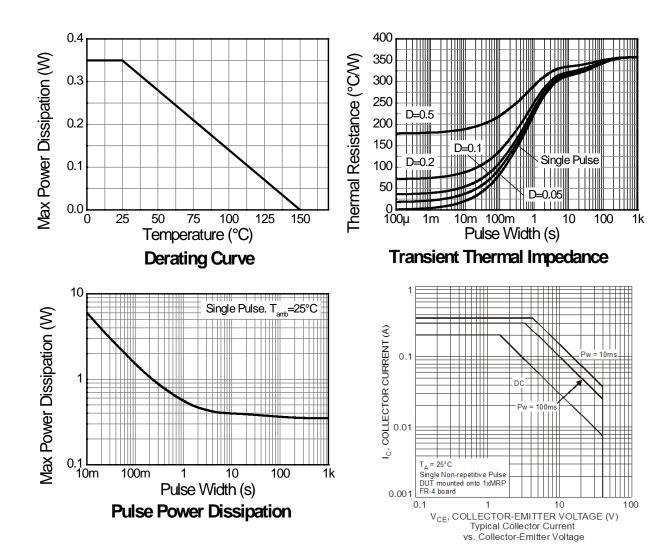
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge—Human Body Model	ESD HBM	4000	V	3A
Electrostatic Discharge—Machine Model	ESD MM	400	V	С

Notes:

- 6. For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR4 PCB; the device is measured under still air conditions while operating in a steady-state.
- 7. Same as Note 6 except the device is mounted on 15 mm x 15mm 1oz copper.
- 8. Thermal resistance from junction to solder-point (at the end of the leads).
- 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information





Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS					
Collector-Base Breakdown Voltage	BV_{CBO}	-40	_	V	$I_C = -100\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	-40		V	$I_C = -10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV_{EBO}	-6.0	_	V	$I_E = -100\mu A, I_C = 0$
Collector Cutoff Current	lo-v	_	-50	nA	$V_{CE} = -30V, V_{BE} = 3.0V$
Collector Cutoff Current	I _{CEV}		-50	nA	$V_{CE} = -30V, V_{BE} = -0.25V$
Emitter-Base Cutoff Current	I _{EBO}	_	-50	nA	$V_{EB} = -5V$
ON CHARACTERISTICS (Note 10)			•	1	
DC Current Gain	h _{FE}	60 80 100 60 30	 300 	l	$\begin{split} I_C &= -100 \mu A, V_{CE} = -1.0 V \\ I_C &= -1.0 m A, V_{CE} = -1.0 V \\ I_C &= -10 m A, V_{CE} = -1.0 V \\ I_C &= -50 m A, V_{CE} = -1.0 V \\ I_C &= -100 m A, V_{CE} = -1.0 V \end{split}$
Collector-Emitter Saturation Voltage	V _{CE(sat)}	_	-0.25 -0.40	V	$I_C = -10\text{mA}, I_B = -1.0\text{mA}$ $I_C = -50\text{mA}, I_B = -5.0\text{mA}$
Base-Emitter Saturation Voltage	V _{BE(sat)}	-0.65 —	-0.85 -0.95	V	$I_C = -10mA$, $I_B = -1.0mA$ $I_C = -50mA$, $I_B = -5.0mA$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{obo}	_	4.5	pF	$V_{CB} = -5.0V$, $f = 1.0MHz$, $I_E = 0$
Input Capacitance	C _{ibo}	_	10	pF	$V_{EB} = -0.5V$, $f = 1.0MHz$, $I_{C} = 0$
Input Impedance	h _{ie}	2.0	12	kΩ	
Voltage Feedback Ratio	h _{re}	0.1	10	× 10 ⁻⁴	$V_{CE} = 10V, I_{C} = 1.0mA,$
Small Signal Current Gain	h _{fe}	100	400	_	f = 1.0kHz
Output Admittance	h _{oe}	3.0	60	μS	
Current Gain-Bandwidth Product	f⊤	250		MHz	$V_{CE} = -20V, I_{C} = -10mA,$ f = 100MHz
Noise Figure	NF	_	4.0	dB	$V_{CE} = -5.0V$, $I_{C} = -100\mu A$, $R_{S} = 1.0k\Omega$, $f = 1.0kHz$
SWITCHING CHARACTERISTICS					
Delay Time	t _d		35	ns	$V_{CC} = -3.0V, I_{C} = -10mA,$
Rise Time	t _r		35	ns	$V_{BE(off)} = 0.5V, I_{B1} = -1.0mA$
Storage Time	ts	_	225	ns	$V_{CC} = -3.0V, I_{C} = -10mA,$
Fall Time	t _f		75	ns	$I_{B1} = I_{B2} = -1.0 \text{mA}$

Note:

10. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



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Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

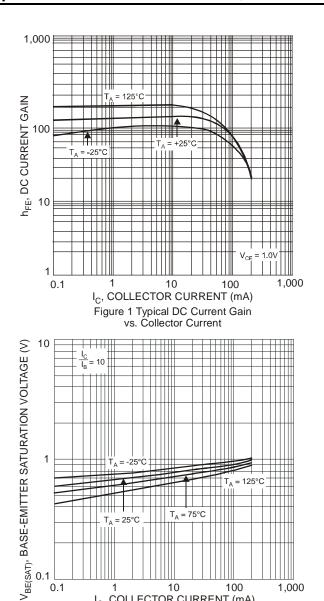


Figure 3 Typical Base-Emitter Saturation Voltage vs. Collector Current

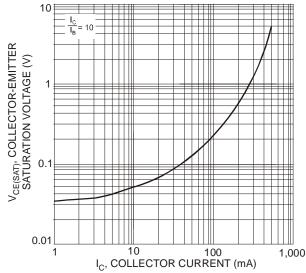


Figure 2 Typical Collector-Emitter Saturation Voltage vs. Collector Current

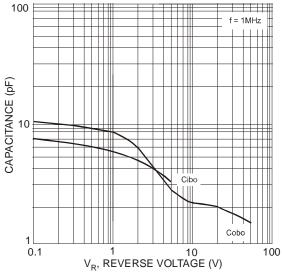


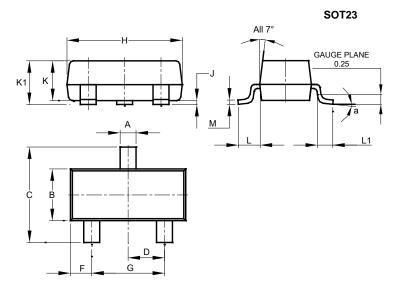
Figure 4 Typical Capacitance Characteristics

1,000



Package Outline Dimensions

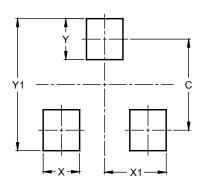
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
C	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
7	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а	0°	8°					
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23

Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	29



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